

IN THE CLAIMS:

Claims 1-10, and 12-27 have been amended. All of the pending claims 1 through 27 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

1. (Currently Amended) A method of fabricating a substrate assembly, comprising:  
providing a substrate having a first surface and an opposing second surface;  
forming a layer of resilient conductive material on at least a portion of at least one of said the  
first and second surfaces of said the substrate;  
forming at least one electrically isolated spring-biased electrical contact in said the layer of  
resilient conductive material;  
forming at least one electrically isolated conductive trace in said the layer of resilient conductive  
material, said the at least one electrically isolated conductive trace having an end  
terminating at said the at least one electrically isolated spring-biased electrical contact;  
and  
treating said the layer of resilient conductive material after said forming said the at least one  
electrically isolated spring-biased electrical contact to achieve at least one desired  
physical characteristic of said the layer of resilient conductive material.

2. (Currently Amended) The method of claim 1, wherein said forming a layer of  
resilient conductive material on at least a portion of at least one of said the first and second  
surface of said the substrate comprises:  
providing a laminate sheet of said the resilient conductive material; and  
bonding said the laminate sheet to said the at least one of said the first and second surfaces of  
said the substrate.

3. (Currently Amended) The method of claim 2, wherein said bonding said the  
laminate sheet to said the at least one of said the first and second surfaces of said the substrate

comprises adhering ~~said the~~ laminate sheet to ~~said the~~ at least one of ~~said the~~ first and second surfaces of ~~said the~~ substrate using an adhesive or bonding ~~said the~~ laminate sheet to ~~said the~~ at least one of ~~said the~~ first and second surfaces of ~~said the~~ substrate using a thermocompression bonding process.

4. (Currently Amended) The method of claim 1, wherein ~~said~~ forming a layer of resilient conductive material on at least a portion of at least one of ~~said the~~ first and second surfaces of ~~said the~~ substrate comprises forming ~~said the~~ layer of resilient conductive material on ~~said the~~ at least one of ~~said the~~ first and second surfaces of ~~said the~~ substrate using a deposition process.

5. (Currently Amended) The method of claim 4, wherein ~~said the~~ deposition process comprises chemical vapor deposition or sputtering.

6. (Currently Amended) The method of claim 1, further comprising forming at least one via in ~~said the~~ substrate, ~~said the~~ at least one via underlying ~~said the~~ at least one electrically isolated spring-biased electrical contact.

7. (Currently Amended) The method of claim 6, wherein ~~said~~ forming at least one via in ~~said the~~ substrate further comprises forming a via opening only to ~~said the~~ at least one of ~~said the~~ first and second surfaces of ~~said the~~ substrate.

8. (Currently Amended) The method of claim 1, further comprising preforming ~~said the~~ at least one electrically isolated spring-biased electrical contact to include a permanent deflection.

9. (Currently Amended) The method of claim 1, further comprising forming at least one contact element on a surface of ~~said the~~ at least one electrically isolated spring-biased electrical contact.

10. (Currently Amended) The method of claim 9, wherein ~~said~~-forming at least one contact element further comprises forming a plurality of alternating grooves and ridges, forming at least one protrusion, or forming a roughened surface.

11. (Original) The method of claim 10, wherein forming a plurality of alternating grooves and ridges, forming at least one protrusion or forming a roughened surface is effected by etching.

12. (Currently Amended) The method of claim 1, wherein ~~said~~-forming at least one electrically isolated spring-biased electrical contact in ~~said the~~ layer of resilient conductive material comprises forming a cantilevered spring, forming a transversely deflecting hoop-shaped spring, forming a spiral-shaped spring, or forming a rosette spring.

13. (Currently Amended) The method of claim 1, wherein at least one of forming at least one electrically isolated spring-biased electrical contact in ~~said the~~ layer of resilient conductive material and forming at least one electrically isolated conductive trace in ~~said the~~ layer of resilient conductive material is effected by etching ~~said the~~ layer of resilient conductive material.

14. (Currently Amended) A method of fabricating a substrate assembly, comprising: providing a substrate having a first surface and an opposing second surface; forming a layer of resilient conductive material on at least a portion of at least one of ~~said the~~ first and second surfaces of ~~said the~~ substrate, ~~said the~~ resilient conductive material exhibiting at least one first physical characteristic;

forming at least one electrically isolated spring-biased electrical contact in-said the layer of resilient conductive material;

forming at least one electrically isolated conductive trace in-said the layer of resilient conductive material, said the at least one electrically isolated conductive trace having an end terminating at-said the at least one electrically isolated spring-biased electrical contact; and

treating-said the layer of resilient conductive material to achieve at least one second physical characteristic of-said the resilient conductive material.

15. (Currently Amended) The method of claim 14, wherein-said the at least one first physical characteristic is selected to optimize properties of-said the layer of resilient conductive material for-said the act of forming at least one electrically isolated spring-biased electrical contact therein.

16. (Currently Amended) The method of claim 14, wherein-said the at least one second physical characteristic is selected to optimize spring characteristics of-said the at least one electrically isolated spring-biased electrical contact.

17. (Currently Amended) The method of claim 14, wherein at least one of forming at least one electrically isolated spring-biased electrical contact in-said the layer of resilient conductive material and forming at least one electrically isolated conductive trace in-said the layer of resilient conductive material is effected by etching-said the layer of resilient conductive material.

18. (Currently Amended) The method of claim 1, further including disposing a dielectric layer overlying-said the layer of resilient conductive material, said the dielectric layer being formed with at least one aperture therethrough substantially aligned with-said the at least one electrically isolated spring-biased electrical contact.

19. (Currently Amended) The method of claim 18, further comprising forming-said the dielectric layer to be of sufficient thickness to encompass at least a portion of each lead element of an integrated circuit device contacting-said the at least one electrically isolated spring-biased electrical contact.

20. (Currently Amended) The method of claim 18, further including forming-said the at least one aperture to be of frustoconical configuration.

21. (Currently Amended) The method of claim 18, further including preforming-said the dielectric layer with-said the at least one aperture prior to disposing-said the dielectric layer over-said the layer of resilient conductive material.

22. (Currently Amended) The method of claim 18, further including forming-said the dielectric layer in place over-said the layer of resilient conductive material and subsequently forming-said the at least one aperture therethrough.

23. (Currently Amended) The method of claim 14, further including disposing a dielectric layer over-said the layer of resilient conductive material, -said the dielectric layer being formed with at least one aperture therethrough substantially aligned with-said the at least one electrically isolated spring-biased electrical contact.

24. (Currently Amended) The method of claim 23, further comprising forming-said the dielectric layer to be of sufficient thickness to encompass at least a portion of each lead element of an integrated circuit device contacting-said the at least one electrically isolated spring-biased electrical contact.

25. (Currently Amended) The method of claim 24, further including forming-said the at least one aperture to be of frustoconical configuration.

26. (Currently Amended) The method of claim 23, further including preforming ~~said~~ the dielectric layer with ~~said~~ the at least one aperture prior to disposing ~~said~~ the dielectric layer over ~~said~~ the layer of resilient conductive material.

27. (Currently Amended) The method of claim 23, further including forming ~~said~~ the dielectric layer in place over ~~said~~ the layer of resilient conductive material and subsequently forming ~~said~~ the at least one aperture therethrough.